

PATENT APPLICATION

Atty. Docket No.: 4591-170
 Applicant: Jong-ho LEE and Nae-In LEE
 Filing Date: February 2, 2001

Serial No. Not Yet Assigned
 Group: Not Yet Assigned

JG971 U.S. PTO
 09/776059

 02/02/01

**INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)**

U.S. PATENT DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Document Number</u>	<u>Issue Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub-Class</u>
—	—	—	—	—	—	—

FOREIGN PATENT DOCUMENTS

	<u>Document Number</u>	<u>Publication Date</u>	<u>Country</u>	<u>Name</u>
D40 7	EP 0851473A2	07/01/1998	EPO	Kizllyall
—	WO 00/01008	01/06/2000	PCT	Lam Research Corp.
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OTHER DOCUMENTS

Exam Init Ref (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner: Roger Wille

Date Considered: 25 Mar 04



PATENT APPLICATION

Docket No.: 4591-170
Applicant: Jong-ho LEE, et al.
Filing Date: February 1, 2001

Serial No. 09/776,059
Group: 1773

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)

U.S. PATENT DOCUMENTS

Exam Init	Ref	Document Number	Issue Date	Name	Class	Sub- Class
<i>Dh</i>	—	5,923,056	07/13/99	Lee, et al.		
—	—	6,013,553	01/11/00	Wallace, et al.		
—	—	6,020,024	02/01/00	Maiti, et al.		
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— — Wilk, G.D. and Wallace, R.M.; "Electrical Properties of hafnium silicate gate dielectrics deposited directly on silicon"; Applied Physics Letters; pp 2854-2856 (1999)

not provided

Examiner: Douglas Wilko

Date Considered: 25 Mar 04